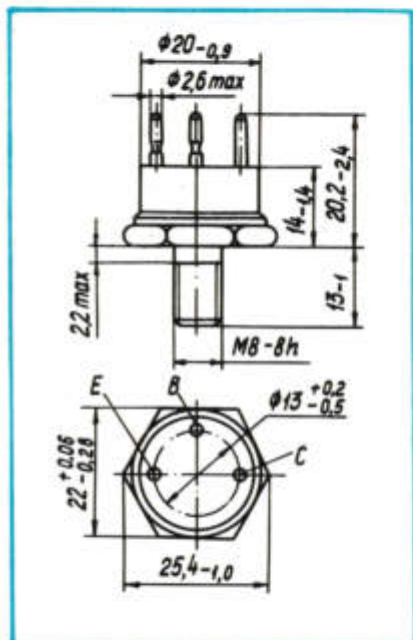


# КТ 944А



БОЛЬШОЙ МОЩНОСТИ ВЫСОКОЙ ЧАСТОТЫ  
HIGH POWER HIGH FREQUENCY



## ОБЩИЕ СВЕДЕНИЯ

Кремниевый эпитаксиально-планарный n-p-n линейный транзистор КТ944А предназначен для работы в аппаратуре широкого применения.

Оформление - в металлокерамическом корпусе.

Диапазон допустимых рабочих температур от -45 до +100°C.

## GENERAL DESCRIPTION

The KT944A transistors are Silicon planar-epitaxial n-p-n linear transistors designed for use in equipment in a wide range of applications.

The devices are encapsulated in metal-ceramic cases.

Allowable operating temperatures: -45 to +100°C.

## ОСНОВНЫЕ ТЕХНИЧЕСКИЕ ДАННЫЕ BASIC TECHNICAL CHARACTERISTICS

### ПРЕДЕЛЬНЫЕ ЗНАЧЕНИЯ ДОПУСТИМЫХ РЕЖИМОВ ЭКСПЛУАТАЦИИ MAXIMUM VALUES OF ALLOWABLE OPERATING CONDITIONS

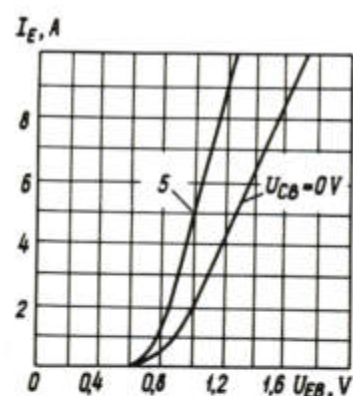
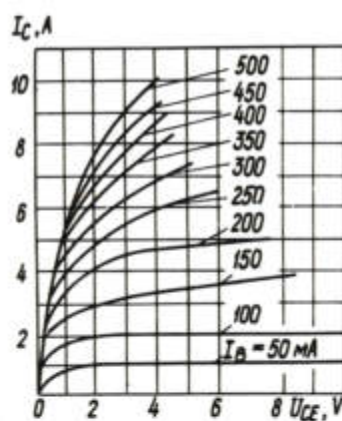
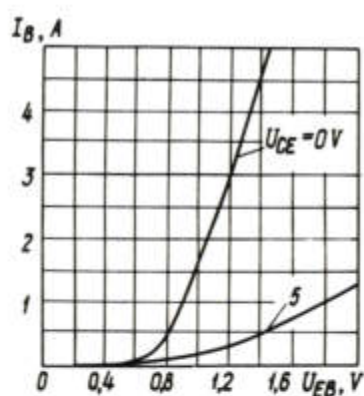
|                                                       |        |
|-------------------------------------------------------|--------|
| $U_{CE \max}$ ( $R_{BE} = 10 \Omega$ )                | 100 V  |
| $U_{EB \max}$                                         | 5 V    |
| $I_C \max$                                            | 12,5 A |
| $I_{CM \max}$ ( $t_p < 1 \text{ ms}$ , $Q \geq 2,5$ ) | 20 A   |
| $I_B \max$                                            | 5 A    |
| $I_{BM \max}$ ( $t_p < 1 \text{ ms}$ , $Q \geq 2,5$ ) | 10 A   |
| $P_C \max^*$ ( $t_{case} \leq 90^\circ \text{C}$ )    | 55 W   |
| $t_j \max$                                            | 175°C  |

\* При  $25 \leq t_{amb} \leq 100^\circ \text{C} \Rightarrow P_C \max = \frac{t_j \max - t_{case}}{R_{thjc}}$

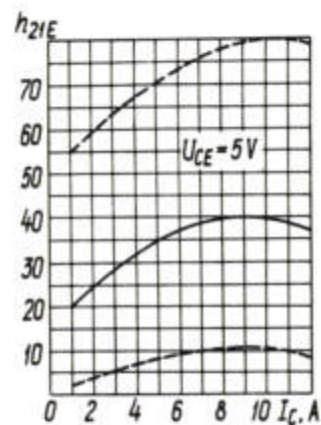
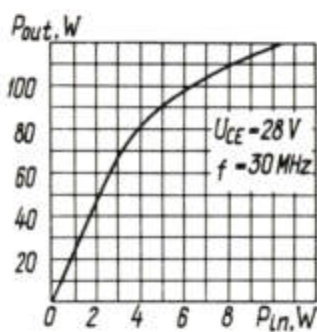
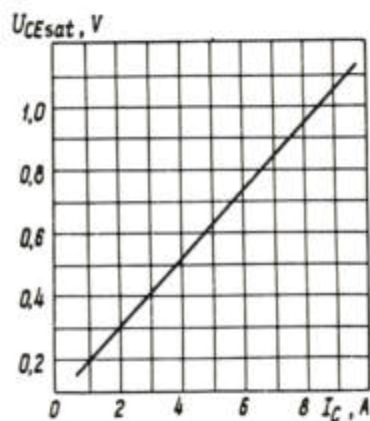
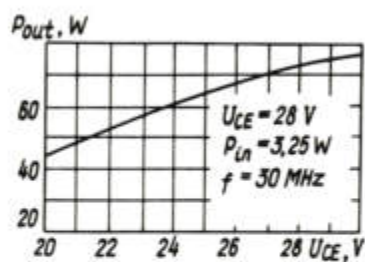
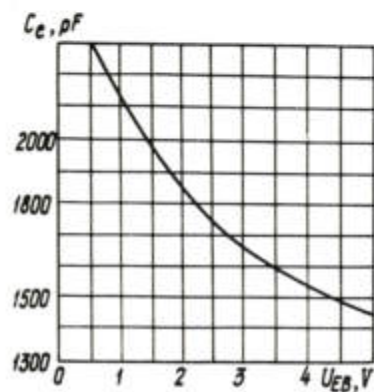
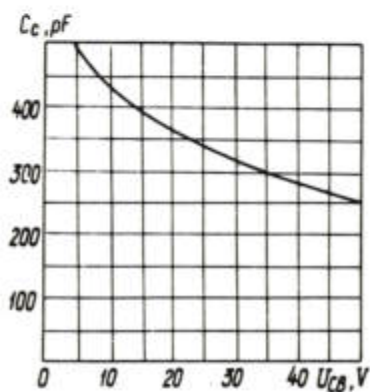
# КТ944А

## ЭЛЕКТРИЧЕСКИЕ ПАРАМЕТРЫ ELECTRICAL PARAMETERS

| Параметры<br>Parameters | Значения<br>Values | Режимы измерений<br>Measuring conditions |                 |          |                  |
|-------------------------|--------------------|------------------------------------------|-----------------|----------|------------------|
|                         |                    | $U_{EB}; U_{CE}^*$<br>$U_{CB}^{**}, V$   | $I_C; I_B^*, A$ | $f, MHz$ | $R_{BE}, \Omega$ |
| $I_{CER}, mA$           | $\leq 80$          | $100^*$                                  |                 |          | 10               |
| $I_{EBO}, mA$           | $\leq 150$         | 5                                        |                 |          |                  |
| $h_{21E}$               | 10 - 80            | $5^*$                                    | 10              |          |                  |
| $ h_{21e} $             | 3,5 - 6,0          | $10^*$                                   | 2               | 30       |                  |
| $U_{CE sat}, V$         | 0,5 - 2,5          |                                          | 10; 2           |          |                  |
| $G_P$                   | 10 - 17            | $28^*$                                   |                 | 30       |                  |
| $\eta_C, \%$            | 60 - 75            | $28^*$                                   |                 | 30       |                  |
| $C_c, pF$               | 270 - 400          | $28^{**}$                                |                 |          |                  |
| $C_e, pF$               | 1000 - 2000        | 5                                        |                 |          |                  |
| $P_{out}, W$            | $\geq 100$         | $28^*$                                   |                 | 30       |                  |



# KT944A



ТИПОВАЯ ЗАВИСИМОСТЬ  
TYPICAL DEPENDENCE



ГРАНИЦЫ  
LIMITS OF **95%** РАЗБРОСА  
SPREAD